

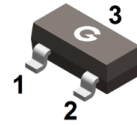
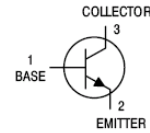
Features

- High DC current gain
- Complimentary to SS8550

HF

Mechanical Data

- Case: SOT-23
- Molding compound: UL flammability classification rating 94V-0
- Terminals: Tin-plated; solderability per MIL-STD-202, Method 208



SOT-23

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
SS8050	SOT-23	3000 pcs / Tape & Reel	Y1

Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Collector-Base Breakdown Voltage	V _{CBO}	40	V
Collector-Emitter Breakdown Voltage	V _{CEO}	25	V
Emitter-Base Breakdown Voltage	V _{EBO}	6	V
Collector Current (Continuous)	I _C	1.5	A
Collector Current (Peak)	I _{CM}	2	A
Power Dissipation	P _D	0.3	W
Junction Temperature Range	T _J	-55 ~ +150	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance Junction-to-Air ^{*1}	R _{θJA}	-	-	350	°C/W
Thermal Resistance Junction-to-Case ^{*1}	R _{θJC}	-	-	150	°C/W
Thermal Resistance Junction-to-Lead ^{*1}	R _{θJL}	-	-	125	°C/W

Note 1: The data tested by surface mounted on a minimum recommended FR-4 board

Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 100\mu\text{A}, I_E = 0$	40	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 0.1\text{mA}, I_B = 0$	25	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 100\mu\text{A}, I_C = 0$	6	-	-	V
Collector Cut-off Current	I_{CBO}	$V_{CB} = 35\text{V}, I_E = 0$	-	-	0.1	μA
Collector Cut-off Current	I_{CEO}	$V_{CE} = 20\text{V}, I_B = 0$	-	-	0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 6\text{V}, I_C = 0$	-	-	0.1	μA
DC Current Gain	h_{FE}	$V_{CE} = 1\text{V}, I_C = 0.1\text{A}$	120	-	400	-
		$V_{CE} = 1\text{V}, I_C = 0.8\text{A}$	40	110	-	-
Collector-emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 0.8\text{A}, I_B = 0.08\text{A}$	-	0.28	0.5	V
Base-emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 0.8\text{A}, I_B = 0.08\text{A}$	-	0.98	1.2	V
Base-emitter on Voltage	$V_{BE(on)}$	$V_{CE} = 1\text{V}, I_C = 10\text{mA}$	-	0.66	1	V
Transition Frequency	f_T	$I_C = 50\text{mA}, V_{CE} = 10\text{V}$	100	190	-	MHz
Collector Output Capacitance	C_{OB}	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$	-	9	-	pF

Classification of h_{FE}

Rank	L	H	J
Range	120-200	200-350	300-400

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

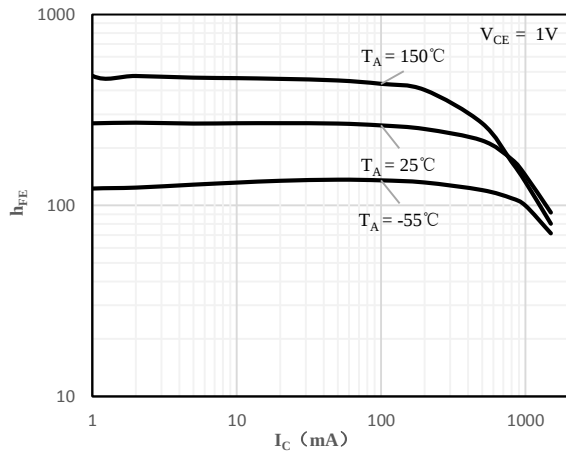


Fig 1 h_{FE} vs. I_C (H)

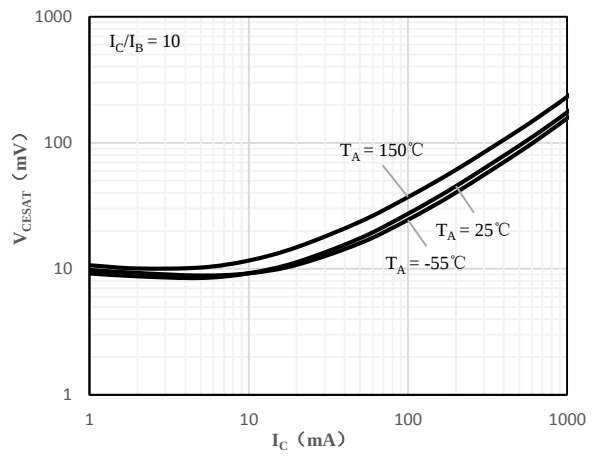


Fig 2 $V_{CE(sat)}$ vs. I_C

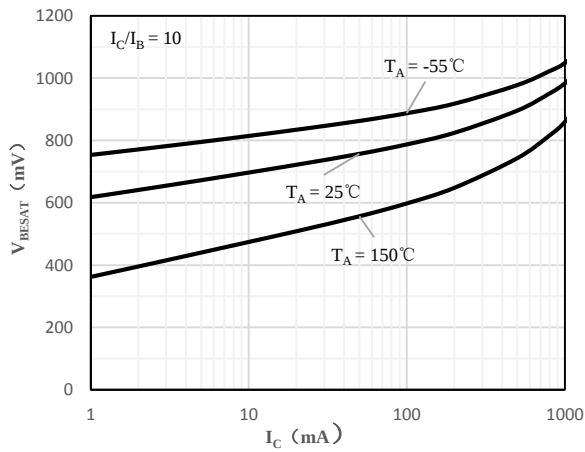


Fig 3 $V_{BE(sat)}$ vs. I_C

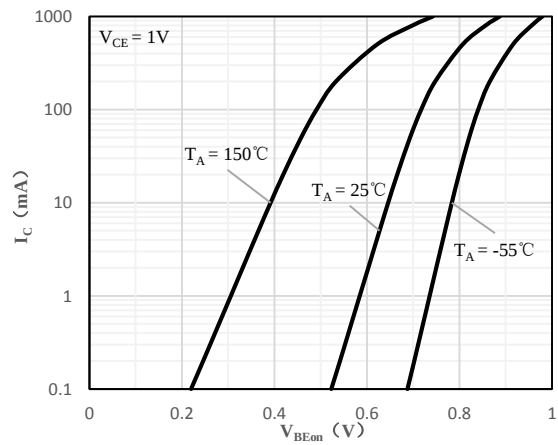


Fig 4 $V_{BE(on)}$ vs. I_C

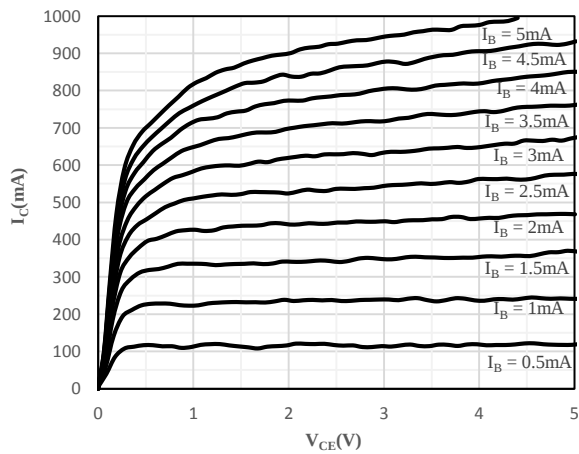


Fig 5 I_C vs. V_{CE}

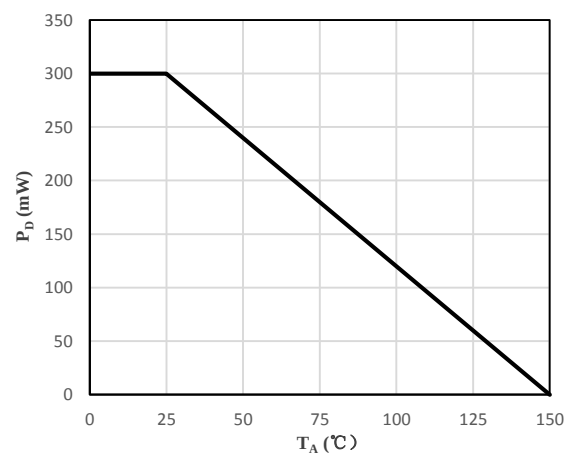
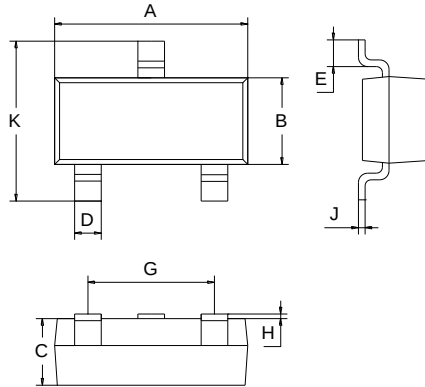


Fig 6 Steady State Power Derating

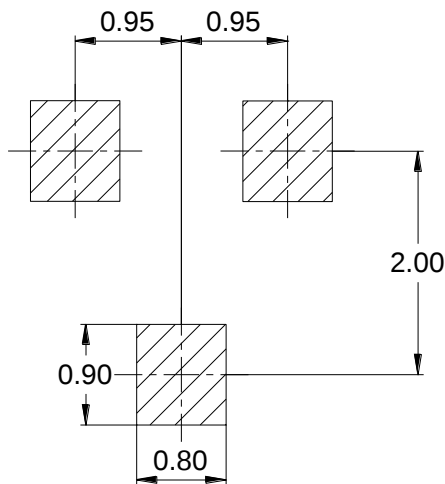
Package Outline Dimensions (Unit: mm)



SOT-23		
Dimension	Min.	Max.
A	2.70	3.10
B	1.10	1.50
C	0.90	1.10
D	0.30	0.50
E	0.35	0.48
G	1.80	2.00
H	0.02	0.10
J	0.05	0.15
K	2.20	2.60

Package Outline Dimensions (Unit: mm)

SOT-23



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